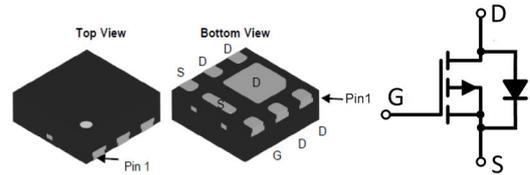


Features

- $V_{DS}=-18V, I_D=-20A$
- $R_{DS(ON)} @V_{GS}=-2.5V, TYP=20m\Omega$
- $R_{DS(ON)} @V_{GS}=-4.5V, TYP=14m\Omega$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Package

DFN2X2-6L



Description

The LX20P18B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

Application

- Electronic cigarette
- Load switch

Ordering information

Order code	Package	Base qty	Delivery mode
LX20P18B	DFN2x2-6L	3K	Tape and reel

Absolute Maximum Ratings (@ $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	-18	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_C=25^\circ C$	-20
		$T_C=100^\circ C$	-10.6
I_{DM}	Pulsed Drain Current	-36	A
P_D	Maximum Power Dissipation	$T_C=25^\circ C$	1.6
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ C/W$
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to 150	$^\circ C$



Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static						
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-15	-18	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -12V, V_{GS} = 0V$	-	-	-1	μV
I_{GSS}	Gate Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.65	-1.0	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_D = -5A$	-	14	23	m Ω
		$V_{GS} = -2.5V, I_D = -4A$	-	20	35	
Dynamic						
C_{iss}	Input Capacitance	$V_{DS} = -10V,$ $V_{GS} = 0V,$ $f = 1.0\text{MHz}$	-	900	-	pF
C_{oss}	Output Capacitance		-	180	-	
C_{riss}	Reverse Transfer Capacitance		-	160	-	
Switching						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = -10V,$ $V_{GS} = -4.5V,$ $R_{GEN} = 6\Omega$	-	15	-	ns
t_r	Turn-On Rise Time		-	35	-	
$t_{d(off)}$	Turn-Off Delay Time		-	30	-	
t_f	Turn-Off Fall Time		-	10	-	
Q_g	Total Gate Charge	$V_{DS} = -4.5V$	-	10	-	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = -10V$	-	2	-	
Q_{gd}	Gate-Drain Charge	$I_D = -5A$	-	3	-	
Drain-source Body diode characteristics						
V_{SD}	Diode Forward Voltage	$I_S = -4.1A, V_{GS} = 0V$	-	-	-1.2	V

Typical Performance Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1 : Power Dissipation

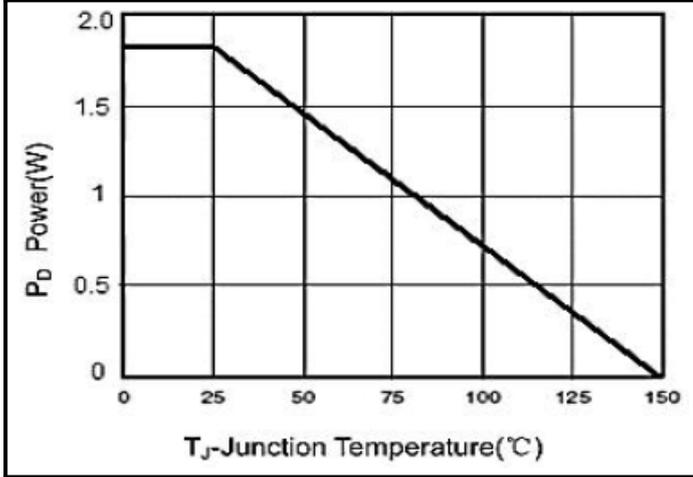


Figure 2 : Drain Current

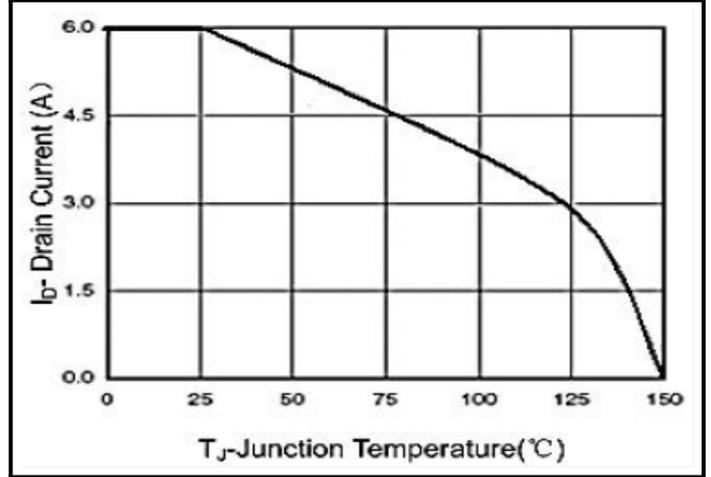


Figure 3 : Output Characteristics

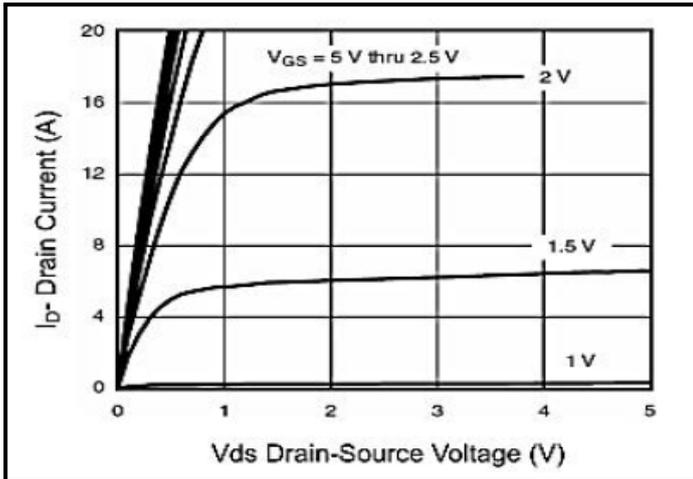


Figure 4 : Drain-Source On-Resistance

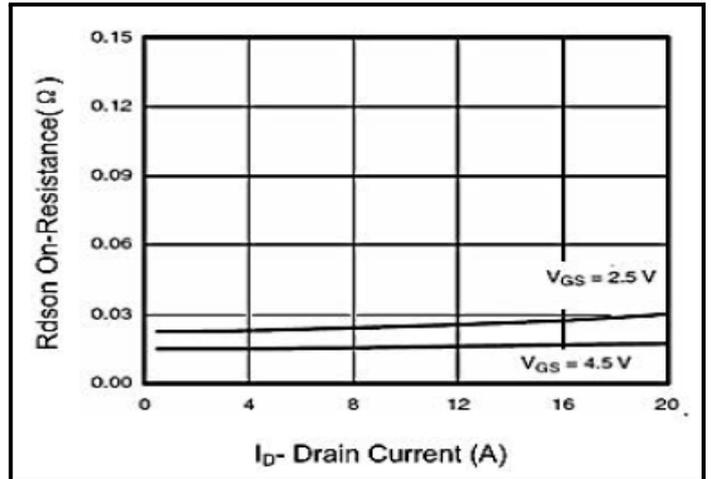


Figure 5 : Transfer Characteristics

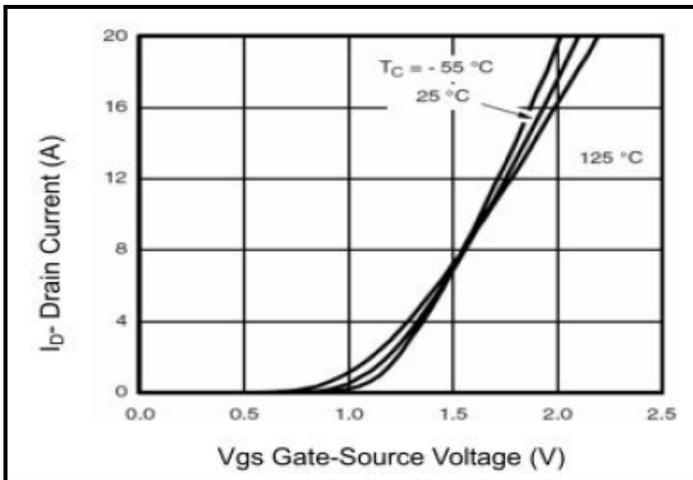
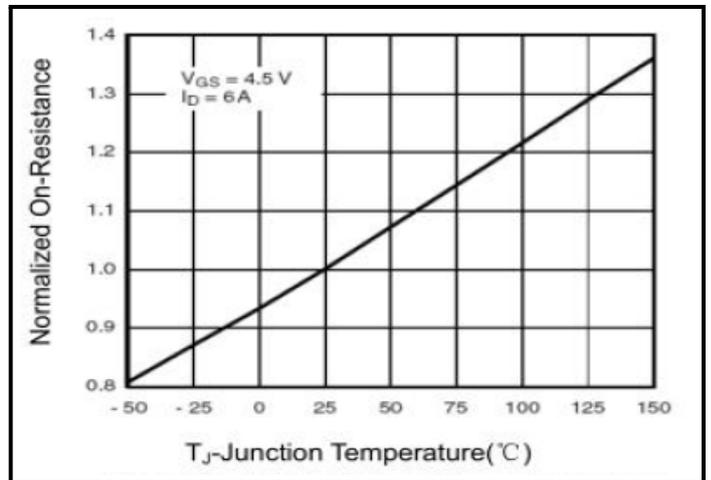


Figure 6 : Drain Current vs. On-resistance



Typical Performance Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 7 : $R_{ds(on)}$ vs. V_{gs}

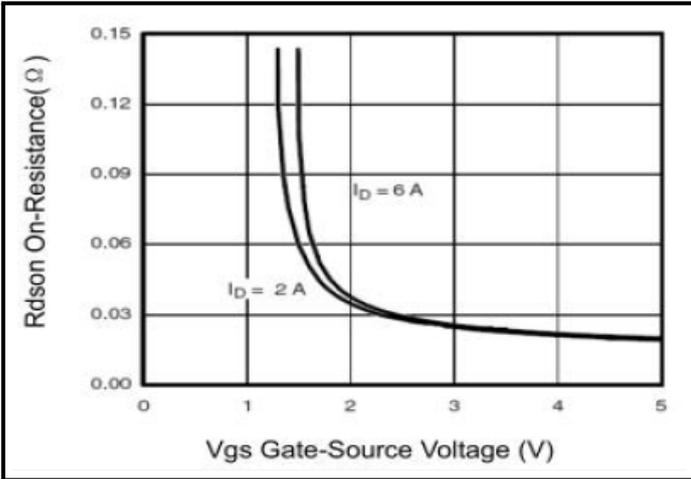


Figure 8 : Capacitance vs. V_{ds}

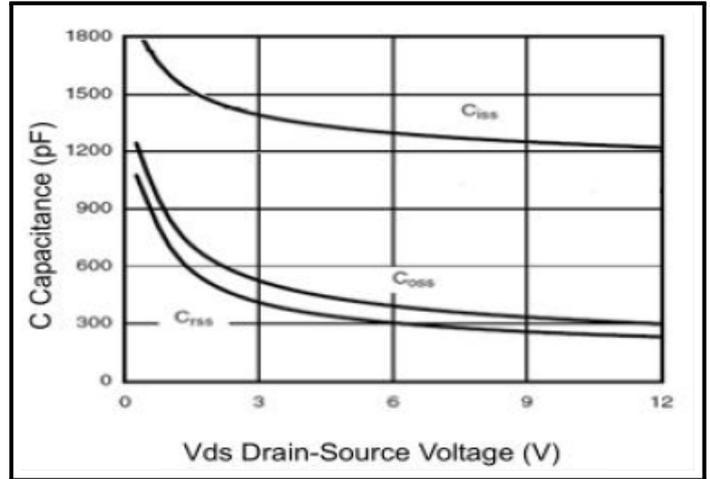


Figure 9 : Gate Charge

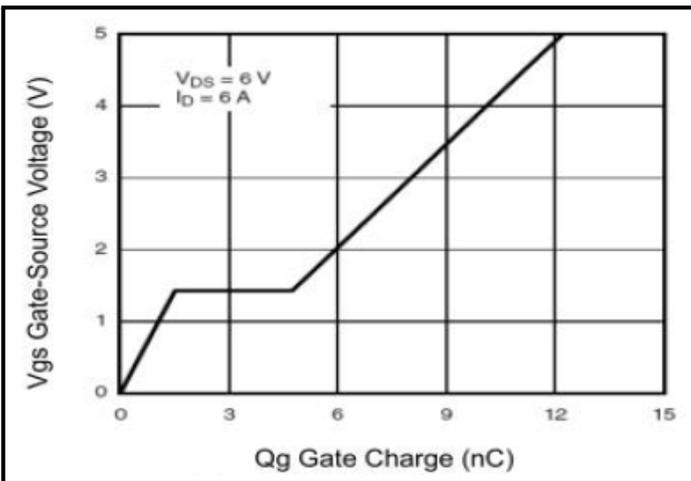


Figure 10 : Source-Drain Diode Forward

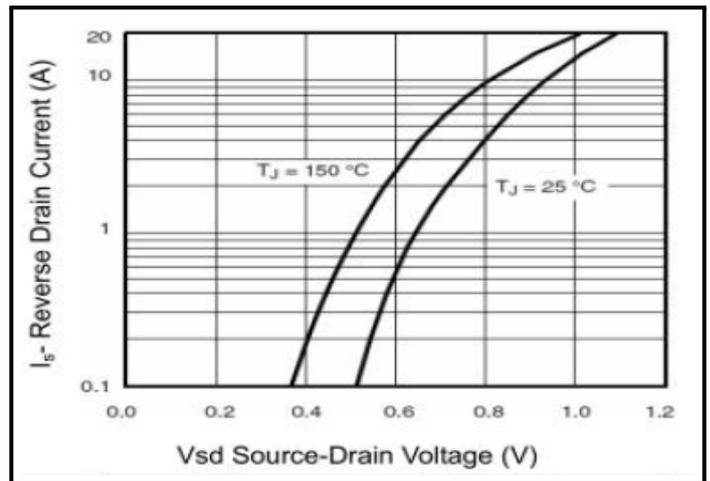
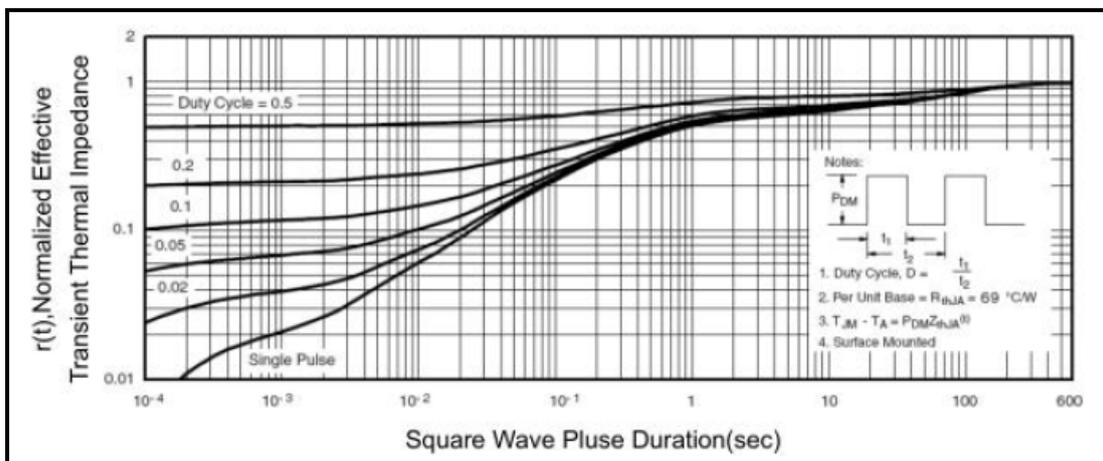
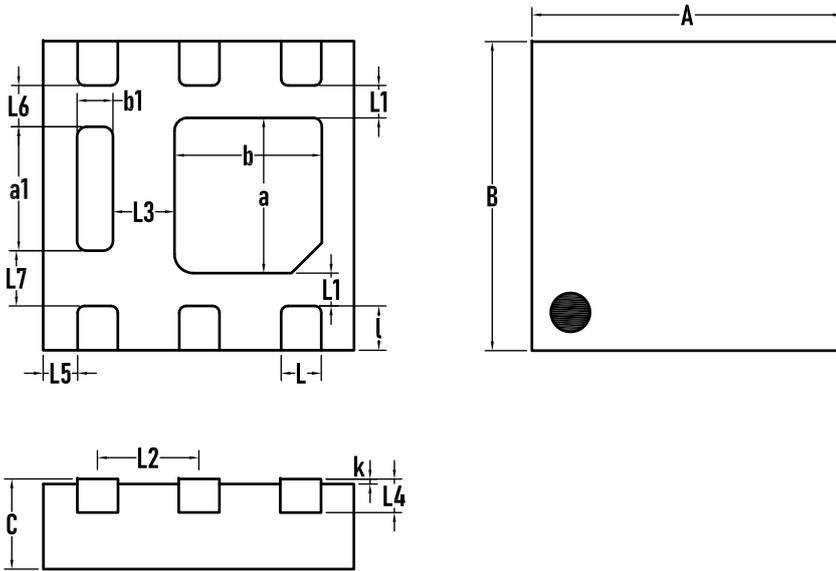


Figure 11 : Normalized Maximum Transient Thermal Impedance



Outline Drawing - DFN2x2-6L



SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	0.25	0.30	0.35
L1	0.10	0.20	0.30
L2	–	0.65	–
L3	0.30	0.40	0.50
L4	–	0.152	–
L5	0.12	0.22	0.32
L6	0.15	0.25	0.35
L7	0.23	0.33	0.43
a	0.90	1.00	1.10
a1	0.72	0.82	0.92
b	0.85	0.95	1.05
b1	0.13	0.23	0.33
l	0.25	0.30	0.35
k	0.00	–	0.05